



DMN5/L06VK/L06VAK/010VAK

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V max
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- ESD Protected up to 2kV
- Qualified to AEC-Q101 standards for High Reliability

Mechanical Data

- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (approximate)













DMN5L06VAK DMN5010VAK

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN5L06VK-7	SOT563	3,000/Tape & Reel
DMN5L06VK-13	SOT563	10,000/Tape & Reel
DMN5L06VAK-7	SOT563	3,000/Tape & Reel
DMN5L06VAK-13	SOT563	10,000/Tape & Reel
DMN5010VAK-7	SOT563	3,000/Tape & Reel
DMN5010VAK-13	SOT563	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information (Note 5)

| D₂ | G₁ | S₁ | KAB YM | S₂ | G₂ | D₁ |

DMN5L06VK

KAB= DMN5L06VK Product Type Marking Code (See Note 5)

YM = Date Code Marking Y = Year (ex: T = 2006)

M = Month (ex: 9 = September)

D₂ S₁ G₁ XXX YM G₂ S₂ D₁

DMN5010VAK DMN5L06VAK

xxx = Product Type Marking Code: KAE or KAC (See Note 5)

YM = Date Code Marking Y = Year (ex: T = 2006)

M = Month (ex: 9 = September)

Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	T	J	٧	W	Х	Y	Z	Α	В	С	D	Е
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Note: 5. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain Source Voltage		V _{DSS}	50	V
Drain-Gate Voltage $R_{GS} \le 1.0 M\Omega$	V_{DGR}	50	V	
Gate-Source Voltage	Continuous Pulsed	V _{GSS}	±20 ±40	V
Drain Current (Note 6)	Continuous Pulsed	I _D I _{DM}	280 1.5	mA A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P_{D}	250	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ heta JA}$	500	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

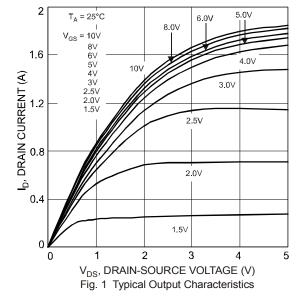
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

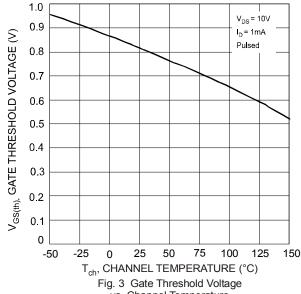
Characterist	ic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage		BV _{DSS}	50	_	_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	@ T _C = +25°C	I _{DSS}	_	_	60	nA	$V_{DS} = 50V, V_{GS} = 0V$
Gate-Body Leakage		I _{GSS}	_	_	1 500 50	μA nA nA	$V_{GS} = \pm 12V, V_{DS} = 0V$ $V_{GS} = \pm 10V, V_{DS} = 0V$ $V_{GS} = \pm 5V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						•	
Gate Threshold Voltage @	$@T_J = +25^{\circ}C$ $T_J = +0^{\circ}C^{\sim} +85^{\circ}C \text{ (Note 8)}$	V _{GS(th)}	0.49 0.30	_	1.0 1.2	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
Static Drain-Source On-Resistance		R _{DS (ON)}		_ _ _	3.0 2.5 2.0	Ω	$V_{GS} = 1.8V$, $I_D = 50$ mA $V_{GS} = 2.5V$, $I_D = 50$ mA $V_{GS} = 5.0V$, $I_D = 50$ mA
On-State Drain Current		I _{D(ON)}	0.5	1.4	_	Α	V _{GS} = 10V, V _{DS} = 7.5V
Forward Transconductance		Y _{fs}	200	_	_	mS	V _{DS} =10V, I _D = 0.2A
Source-Drain Diode Forward Voltage		V_{SD}	0.5	_	1.4	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance		C _{iss}	_	_	50	pF	I
Output Capacitance		Coss	_	_	25	pF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance		C _{rss}	_	_	5.0	pF	1.0111112

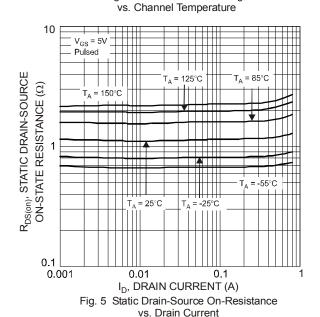
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.7. Short duration pulse test used to minimize self-heating effect.8. Guaranteed by design. Not subject to product testing.

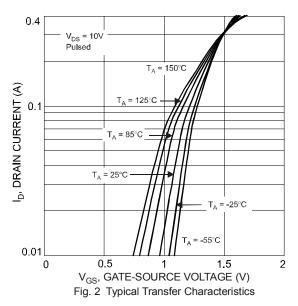












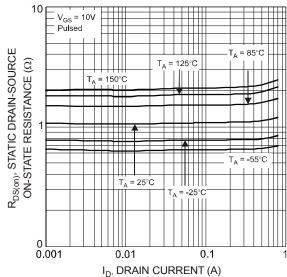
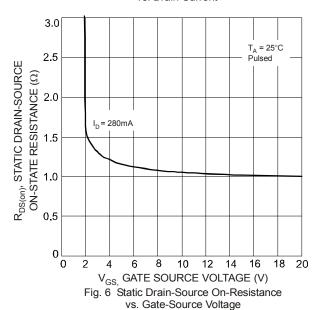


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current







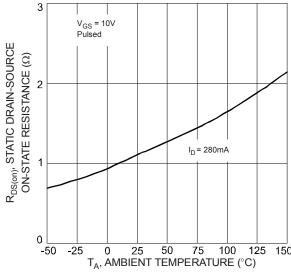
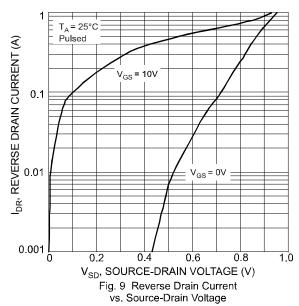
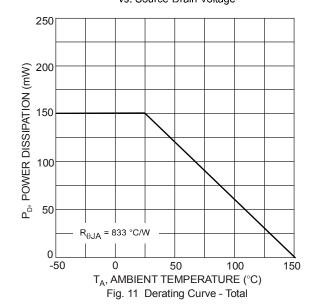
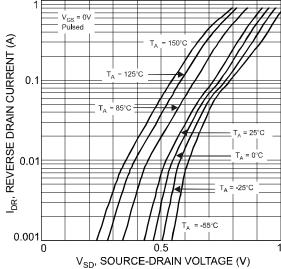


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature







/_{SD}, SOURCE-DRAIN VOLTAGE (Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

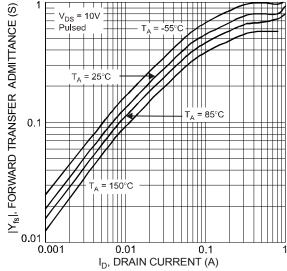
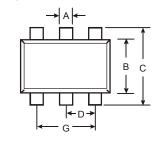


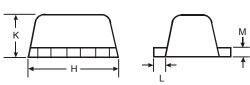
Fig.10 Forward Transfer Admittance vs. Drain Current



Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

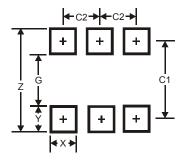




SOT563						
Dim	Min	Max	Тур			
Α	0.15	0.30	0.20			
В	1.10	1.25	1.20			
С	1.55	1.70	1.60			
D	ı	1	0.50			
G	0.90	1.10	1.00			
Н	1.50	1.70	1.60			
K	0.55	0.60	0.60			
L	0.10	0.30	0.20			
М	0.10	0.18	0.11			
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5



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